# Abstracts

## Broadband 0.25 Micron Ion-Implant MMIC Low Noise Amplifiers on GaAs

*J. Sanctuary, C.E. Woodin and J. Manning. "Broadband 0.25 Micron Ion-Implant MMIC Low Noise Amplifiers on GaAs." 1992 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 92.1 (1992 [MCS]): 25-28.*

A highly manufacturable 0.25 micron ion-implant-process has been used for the development of low noise MMIC amplifiers covering the 2-18 GHz band. Noise figures of less than 2.5 dB and 3.0 dB have been achieved with MMICs covering the 2-6 GHz and 6-18 GHz bands respectively. Insertion gains were 16 dB for the 2-6 GHz design and 10 dB for the 6-18 GHz design. This performance is comparable to that reported for HEMT processes.

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